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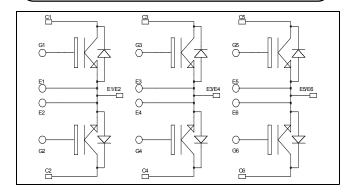
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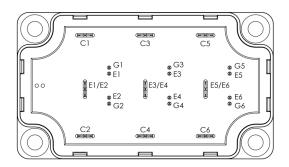
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Triple Dual Common Source Trench + Field Stop IGBT3 Power Module





Absolute maximum ratings

APTGT50TDU60PG

$V_{CES} = 600V$ $I_{C} = 50A$ @ $Tc = 80^{\circ}C$

Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS Compliant

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
	Continuous Conector Current	$T_C = 80^{\circ}C$	50	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V _{GE}	Gate – Emitter Voltage		± 20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	176	W
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^{\circ}C$	100A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
V _{CE(sat)}		$I_C = 50A$	$T_{j} = 150^{\circ}C$		1.7		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600 \mu A$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			3150		pF
C _{oes}	Output Capacitance				200		
C _{res}	Reverse Transfer Capacitance				95		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			110		
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{GE} = 200V$			45		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 500V$ $I_C = 50A$	$V_{Bus} = 300V$ $L_c = 50A$		200		ns
T _f	Fall Time	$R_G = 8.2\Omega$			40		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$ $R_G = 8.2\Omega$			120		ns
T _r	Rise Time				50		
T _{d(off)}	Turn-off Delay Time				250		
T _f	Fall Time				60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.3		mJ
		$V_{Bus} = 300V$	$T_{j} = 150^{\circ}C$		0.43		1113
E _{off}	Turn-off Switching Energy	$\begin{array}{c} I_{C}=50A\\ R_{G}=8.2\Omega \end{array} \qquad \begin{array}{c} T_{j}=25^{\circ}C\\ T_{j}=150^{\circ}C \end{array}$	$T_j = 25^{\circ}C$		1.35		mJ
Loff				1.75		1115	

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$			250	μA
IRM			$T_{j} = 150^{\circ}C$			500	μΛ
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		50		А
V _F	Diode Forward Voltage	$I_{\rm F} = 50 A$ $V_{\rm GE} = 0 V$	$T_i = 25^{\circ}C$		1.6	2	V
v F			$T_{i} = 150^{\circ}C$		1.5		v
t _{rr}	Reverse Recovery Time	$I_{F} = 50A$ $V_{R} = 300V$ $di/dt = 1800A/\mu s$	$T_j = 25^{\circ}C$		100		ns
۲r			$T_{j} = 150^{\circ}C$		150		
0	Reverse Recovery Charge		$T_j = 25^{\circ}C$		2.6		
Q _{rr}			$T_{j} = 150^{\circ}C$		5.4		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		0.6		mJ
Ľr			$T_{j} = 150^{\circ}C$		1.2		IIIJ

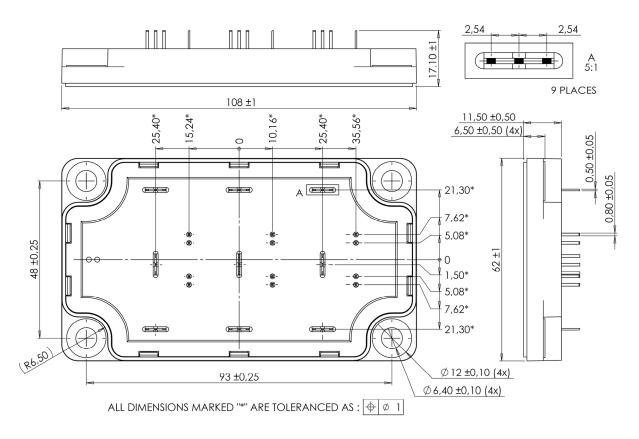


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Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
р	Junction to Case Thermal Resistance		IGBT			0.85	°C/W
R _{thJC} Junction to Case Thermal Resistance			Diode			1.42	C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		175	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

SP6-P Package outline (dimensions in mm)

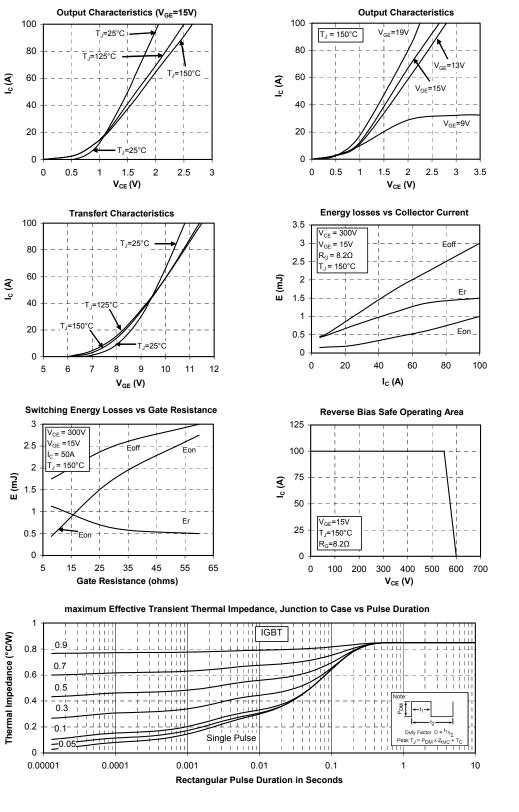


See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

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Typical Performance Curve



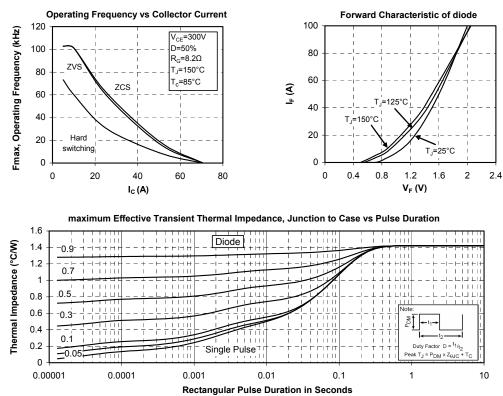
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